

SMB Super Fast Recovery Diode 超快恢复二极管
■Features 特点

Glass passivated chip junction 玻璃钝化芯片保护结

High forward surge capability 高正向浪涌能力

Super Fast Recovery time 超快恢复时间

Surface Mount Device 表面贴装器件

Case 封装:SMB


■Maximum Rating 最大额定值

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MURS320B	MURS340B	MURS360B	Unit 单位
Repetitive Peak Reverse Voltage 重复峰值反向电压	V_{RRM}	200	400	600	V
DC Reverse Voltage 直流反向电压	V_R	200	400	600	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	140	280	420	V
Forward Rectified Output Current 正向整流电流	I_O	3			A
Peak Surge Current 峰值浪涌电流	I_{FSM}	100			A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	60			°C/W
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	-50to+150°C			°C

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MURS320B	MURS340B	MURS360B	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.92	1.25		V	I _F =3A
Reverse Current 反向电流	I _R	5(T _A =25℃) 50(T _A =125℃)			μA	V _R =V _{RRM}
Reverse Recovery Time 反向恢复时间	T _{rr}	35	50		nS	I _F =0.5A,I _R =1A I _{rr} =0.25A
Avalanche energy 雪崩能量	E _{AS}	6.6	4.8		mJ	I _R =0.8A,L=15mH
Junction Capacitance 结电容	C _J	63	55	50	pF	V _R =4V,f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1: Io-TL Curve

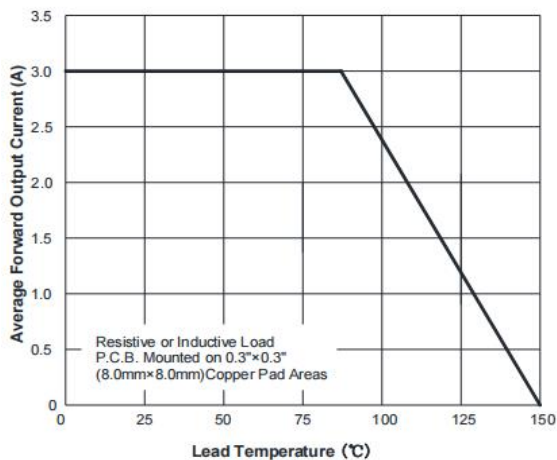


FIG.2: Forward Surge Current Capability

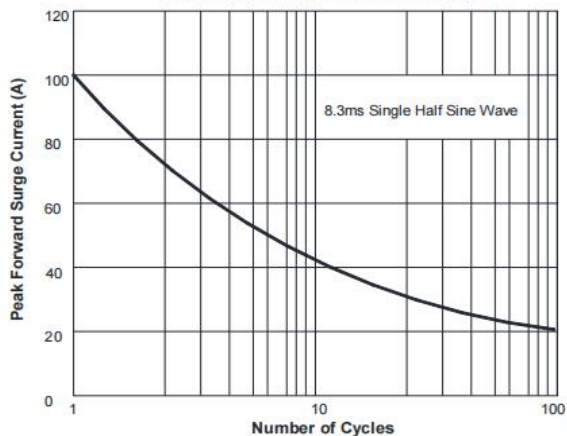


FIG.3: Typical Forward Voltage

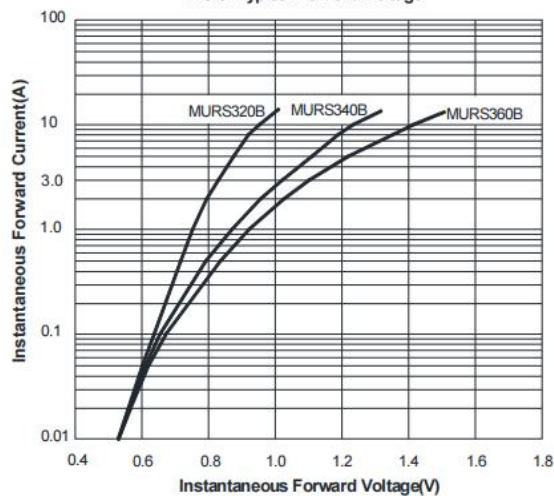


FIG.4: Typical Reverse Characteristics

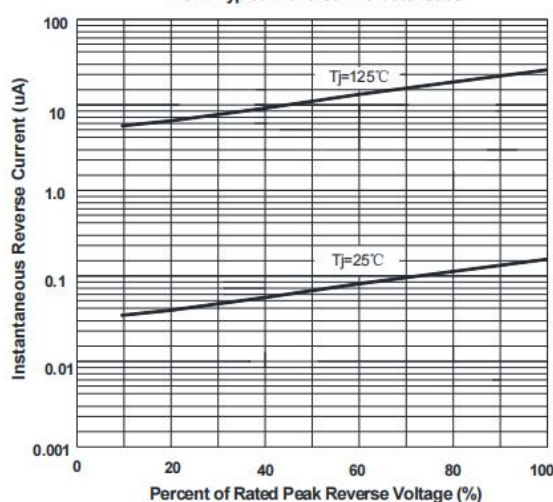
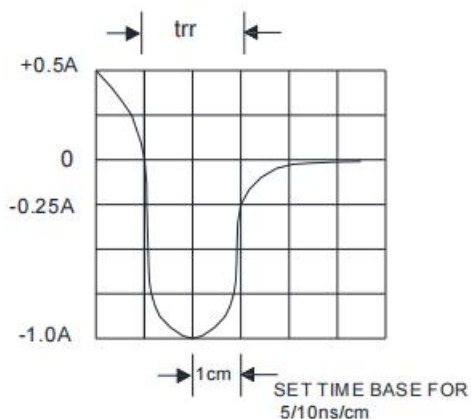
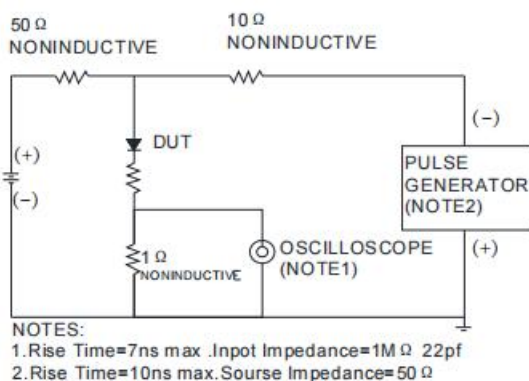
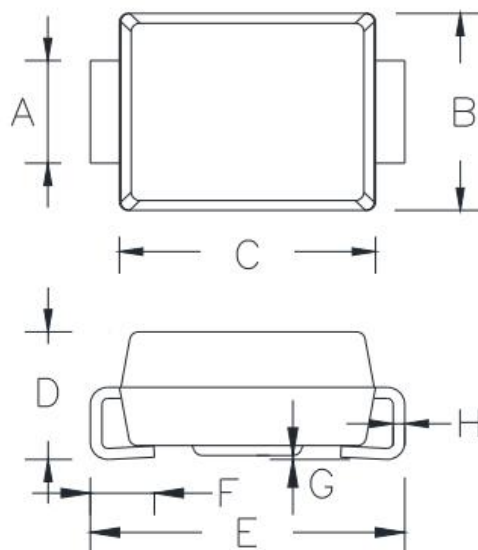


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in millimeters

DO-214AA(SMB)		
Dim	Min	Max
A	1.85	2.15
B	3.30	3.94
C	4.05	4.75
D	1.99	2.61
E	5.21	5.59
F	0.90	1.41
G	0.10	0.20
H	0.15	0.31